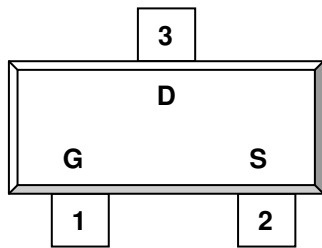


DESCRIPTION

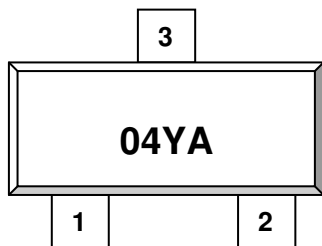
STN1304 is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management, other battery powered circuits, and low in-line power loss are required. The product is in a very small outline surface mount package.

PIN CONFIGURATION
SOT-323


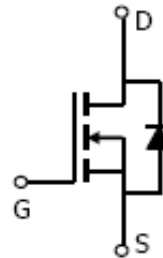
1.Gate 2.Source 3.Drain

FEATURE

- 20V/2.0A, $R_{DS(ON)} = 225m\Omega$ @VGS = 4.5V
- 20V/1.5A, $R_{DS(ON)} = 315m\Omega$ @VGS = 2.5V
- 20V/1.0A, $R_{DS(ON)} = 425m\Omega$ @VGS = 4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-323 package design

PART MARKING
SOT-323


Y: Year Code A: Process Code



**STN1304**

N Channel Enhancement Mode MOSFET

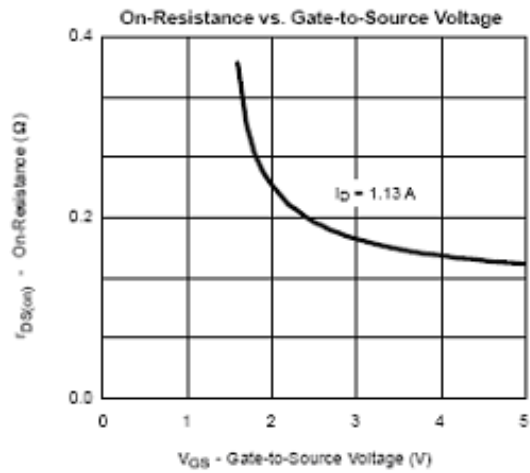
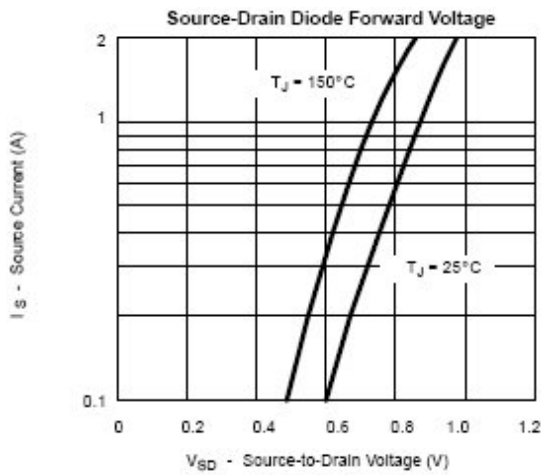
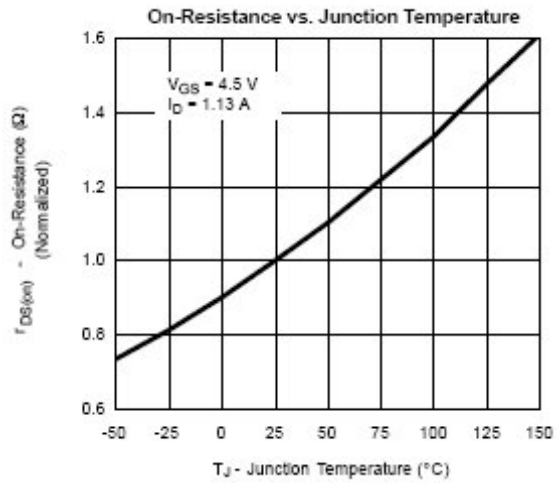
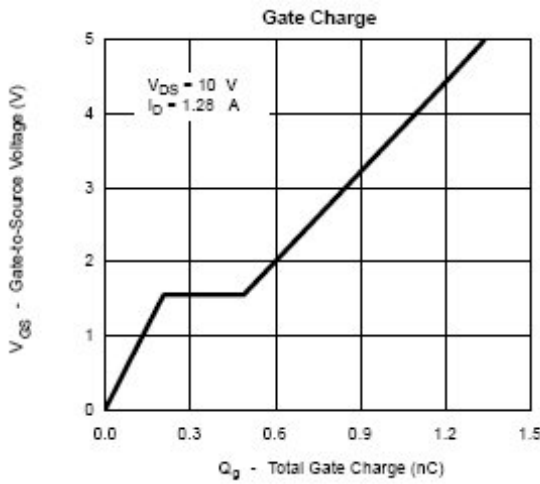
2.0A**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (T _J =150°C)	I _D	T _A =25°C 2.0	A
		T _A =70°C 1.5	
Pulsed Drain Current	I _{DM}	10	A
Continuous Source Current (Diode Conduction)	I _S	1.6	A
Power Dissipation	P _D	T _A =25°C 1.25	W
		T _A =70°C 0.8	
Operation Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	105	°C/W

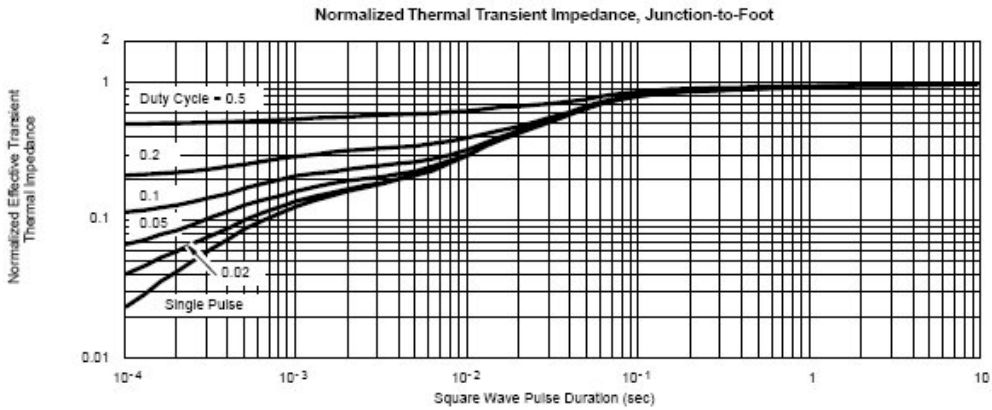
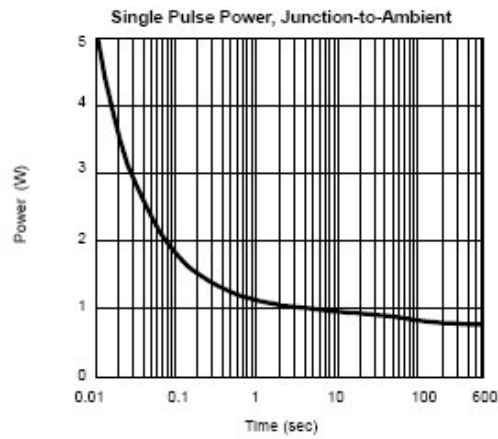
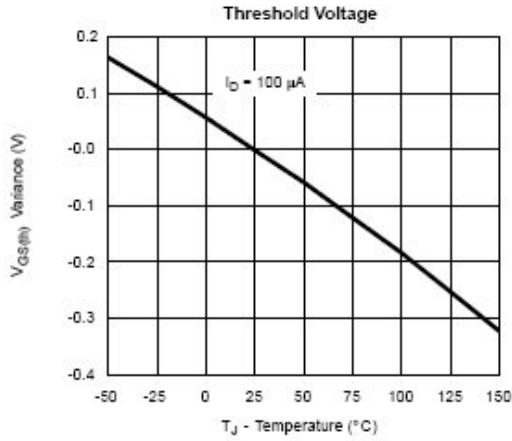
ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

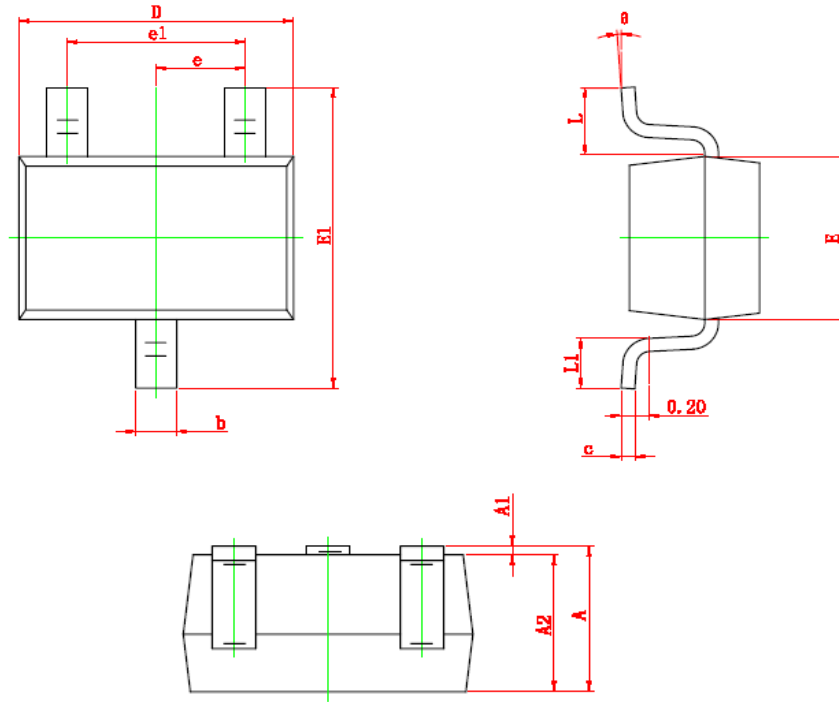
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.35		1.0	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=55^\circ C$			5	
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=2.0A$		0.150	0.225	Ω
		$V_{GS}=2.5V, I_D=1.5A$		0.210	0.315	
		$V_{GS}=1.8V, I_D=1.0A$		0.320	0.425	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=1.2A$		10		S
Diode Forward Voltage	V_{SD}	$I_S=0.5A, V_{GS}=0V$		0.80	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=10V$ $V_{GS}=4.5V$ $I_D=0.7A$		1.2	1.5	nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.3		
Input Capacitance	C_{iss}	$V_{DS}=10V$ $V_{GS}=0V$ $F=1MHz$		110		pF
Output Capacitance	C_{oss}			34		
Reverse Transfer Capacitance	C_{rss}			16		
Turn-On Time	$t_{d(on)}$ t_r	$V_{DD}=10V$ $R_L=10\Omega$ $I_D=1.0A$ $V_{GEN}=4.5V$ $R_G=6\Omega$		5	10	nS
				8	15	
Turn-Off Time	$t_{d(off)}$ t_f			10	18	
				1.2	2.8	

TYPICAL CHARACTERISTICS (25°C Unless noted)



TYPICAL CHARACTERISTICS (25°C Unless noted)



SOT-323 PACKAGE OUTLINE


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°